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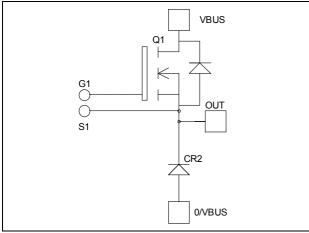






Buck chopper **MOSFET Power Module**

 $V_{DSS} = 1000V$ $I_D = 78A$ @ Tc = 25°C



Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- **RoHS Compliant**

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
$V_{ m DSS}$	Drain - Source Breakdown Voltage	1000	V	
т	Continuous Drain Current	$T_c = 25$ °C	78	
I_D	Continuous Drain Current	$T_c = 80^{\circ}C$	59	A
I_{DM}	Pulsed Drain current		312	
V_{GS}	Gate - Source Voltage	±30	V	
R_{DSon}	Drain - Source ON Resistance		105	$m\Omega$
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		1250	W
I_{AR}	Avalanche current (repetitive and non repetitive)		25	A
E_{AR}	Repetitive Avalanche Energy		50	T
E_{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$ $T_j = 25$	5°C		400	μА
		$V_{GS} = 0V, V_{DS} = 800V$ $T_j = 12$	5°C		2000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 39A$		90	105	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 10$ mA	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±250	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		20.7		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		3.5		nF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		0.64		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		744		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		96		nC
Q_{gd}	Gate – Drain Charge	$I_D = 78A$		488		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		18		
T_{r}	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 670V \\ I_D &= 78A \\ R_G &= 1.2\Omega \end{aligned}$		12		
$T_{d(off)}$	Turn-off Delay Time			155		ns
T_{f}	Fall Time			40		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		3.6		т
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 78A, R_G = 1.2\Omega$		2.5		mJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		5.7		T
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 78A, R_G = 1.2\Omega$		3.1		mJ

Chopper diode ratings and characteristics

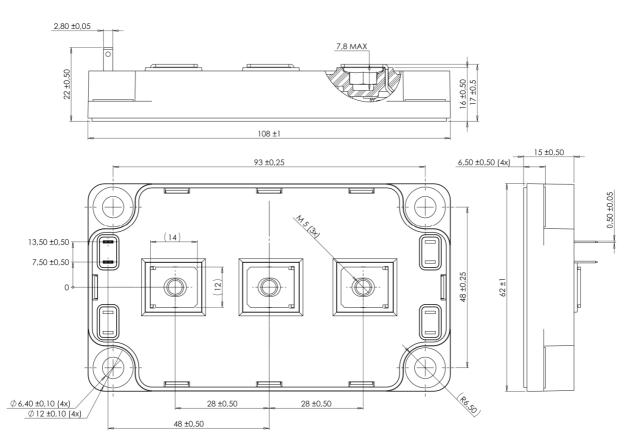
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I_{RM}	Maximum Reverse Leakage Current	$V_{R}=1000V$	$T_j = 25^{\circ}C$			250	μΑ
1KM	Waximam Reverse Bearage Carrent	V R 1000 V	$T_j = 125$ °C			500	μ21
I_{F}	DC Forward Current		$T_c = 70^{\circ}C$		100		A
	Diode Forward Voltage	$I_F = 100A$			1.9	2.5	
$V_{\rm F}$		$I_F = 200A$			2.2		V
		$I_F = 100A$	$T_{j} = 125^{\circ}C$		1.7		
t_{rr}	Reverse Recovery Time		$T_j = 25$ °C		300		ns
ι _{rr}	Reverse Recovery Time	$I_F = 100A$ $V_R = 670V$	$T_{j} = 125^{\circ}C$		360		115
Q_{rr}	Reverse Recovery Charge	$di/dt = 200A/\mu s$	$T_j = 25$ °C		800		nC
	Reverse Recovery Charge		$T_{i} = 125^{\circ}C$		4050		пс



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		Transistor			0.1	
			Diode			0.55	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	11.111
Wt	Package Weight	·	·			300	g

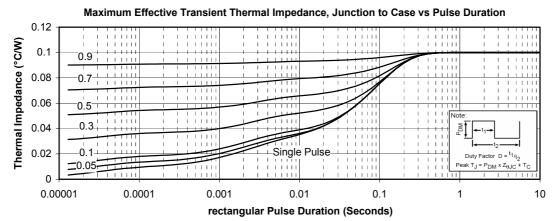
SP6 Package outline (dimensions in mm)

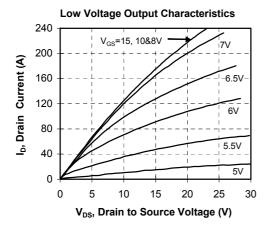


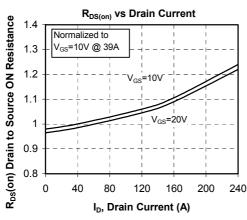
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

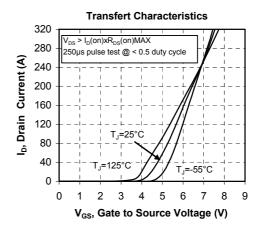


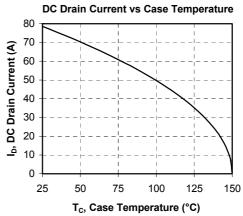
Typical Performance Curve



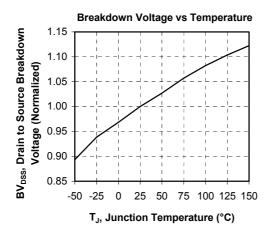


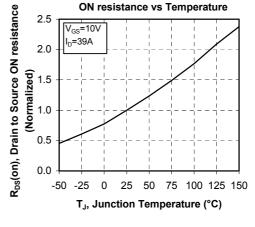


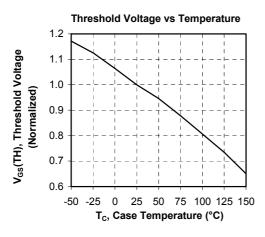


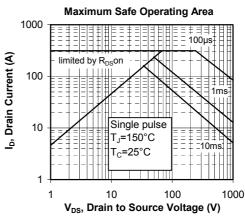


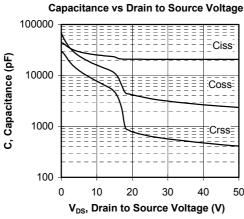


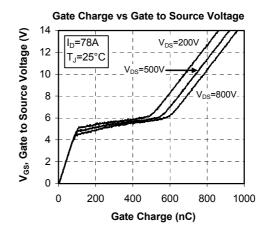




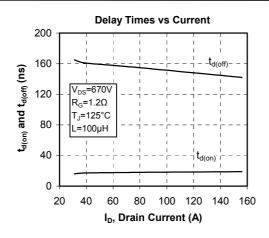


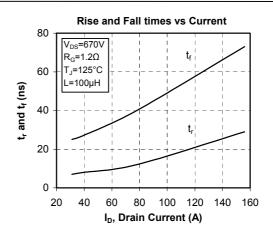


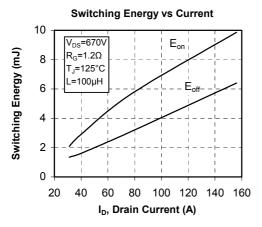


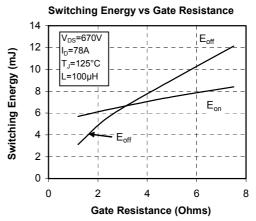


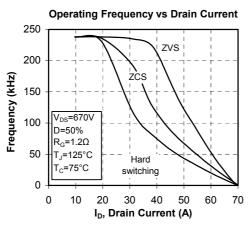


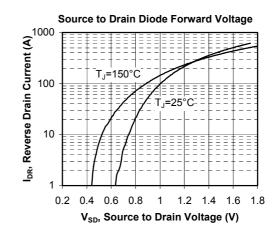














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